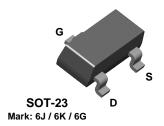


PN4391 PN4392 **PN4393**  MMBF4391 MMBF4392 **MMBF4393** 





NOTE: Source & Drain are interchangeable

### **N-Channel Switch**

This device is designed for low level analog switching, sample and hold circuits and chopper stabalized amplifiers. Sourced from Process 51. See J111 for characteristics.

### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{DG}$	Drain-Gate Voltage	30	V	
V <sub>GS</sub>	Gate-Source Voltage	- 30	V	
I <sub>GF</sub>	Forward Gate Current		mA	
T <sub>J</sub> ,T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

#### **Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	Max Un		Units
		PN4391-4393	*MMBF4391-4393	
$P_D$	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

# N-Channel Switch (continued)

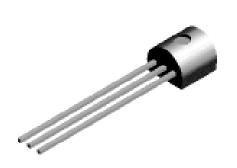
Symbol	Parameter	Test Conditions	i	Min	Max	Units
OFF CHAF	RACTERISTICS					
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	$I_G = 1.0 \mu A, V_{DS} = 0$		- 30		V
I <sub>GSS</sub>	Gate Reverse Current	$V_{GS} = -15 \text{ V}, V_{DS} = 0$			- 1.0	nA
		$V_{GS} = -15 \text{ V}, V_{DS} = 0, T_A = 0$	150°C		- 0.2	μΑ
V <sub>GS(off)</sub>	Gate-Source Cutoff Voltage	$V_{DS} = 20 \text{ V}, I_{D} = 1.0 \text{ nA}$	4391	- 4.0	- 10	V
			4392 4393	- 2.0 - 0.5	- 5.0 - 3.0	V
V <sub>GS(f)</sub>	Gate-Source Forward Voltage	I <sub>G</sub> = 1.0 mA, V <sub>DS</sub> = 0	4333	0.0	1.0	V
I <sub>D(off)</sub>	Drain Cutoff Leakage Current	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = - 12 V	4391		0.1	nA
5(0)		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = -7.0 V	4392		0.1	nA
		$V_{DS} = 20 \text{ V}, V_{GS} = -5.0 \text{ V}$	4393		0.1	nA
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = - 12 V,	1201		0.2	μА
		$T_A = 150$ °C $V_{DS} = 20 \text{ V}, V_{GS} = -7.0 \text{ V},$	4391		0.2	μΛ
		T <sub>A</sub> = 150°C	4392		0.2	μΑ
		$V_{DS} = 20 \text{ V}, V_{GS} = -5.0 \text{ V},$			0.0	
		T <sub>A</sub> = 150°C	4393		0.2	μΑ
ON CHARA	ACTERISTICS					
I <sub>DSS</sub>	Zero-Gate Voltage Drain Current*	$V_{DS} = 20 \text{ V}, V_{GS} = 0$	4391	50	150	mA
		, 50	4392	25	75	mA
			4393	5.0	30	mA
$V_{DS(on)}$	Drain-Source On Voltage	$I_D = 12 \text{ mA}, V_{GS} = 0$	4391		0.4	V
		$I_D = 6.0 \text{ mA}, V_{GS} = 0$ $I_D = 3.0 \text{ mA}, V_{GS} = 0$	4392 4393		0.4 0.4	V
r <sub>DS(on)</sub>	Drain-Source On Resistance	$I_D = 3.0 \text{ mA}, V_{GS} = 0$ $I_D = 1.0 \text{ mA}, V_{GS} = 0$	4391		30	Ω
108(011)	Brain Goards on Recicians	15 - 1.3 m, vgs - 3	4392		60	Ω
			4393		100	Ω
SMALL-SI	GNAL CHARACTERISTICS					
r <sub>ds(on)</sub>	Drain-Source On Resistance	$V_{DS} = V_{GS} = 0$ , f= 1.0 kHz	4391		30	Ω
ids(on)	Train Course on Resistance	1 55 1 65 6, 1 116 11.12	4392		60	Ω
			4393		100	Ω
Ciss	Input Capacitance	$V_{DS} = 20, V_{GS} = 0, f = 1.0 M$	Hz		14	pF
Crss	Reverse Transfer Capacitance	$V_{GS} = -12 \text{ V}, f = 1.0 \text{ MHz}$	4391		3.5	pF
		$V_{GS} = -7.0 \text{ V}, f = 1.0 \text{ MHz}$	4392		3.5 3.5	pF pF
		V <sub>GS</sub> = - 5.0 V, f = 1.0 MHz	4393		3.3	рі
SWITCHI	NG CHARACTERISTICS	_			1	1
t <sub>r</sub>	Rise Time	$I_{D(on)} = 12 \text{ mA}$	4391		5.0	ns
		$I_{D(on)} = 6.0 \text{ mA}$	4392		5.0 5.0	ns ns
tf	Fall Time	$I_{D(on)} = 3.0 \text{ mA}$ $V_{GS(off)} = 12 \text{ V}$	4393		15	ns
	i all lillie	$V_{GS(off)} = 12 V$ $V_{GS(off)} = 6.0 V$	4391 4392		20	ns
		$V_{GS(off)} = 0.0 \text{ V}$ $V_{GS(off)} = 3.0 \text{ V}$	4393		30	ns
ton	Turn-On Time	$I_{D(on)} = 12 \text{ mA}$	4391		15	ns
		$I_{D(on)} = 6.0 \text{ mA}$	4392		15	ns
		$I_{D(on)} = 3.0 \text{ mA}$	4393	<u></u>	15	ns
t <sub>off</sub>	Turn-Off Time	V <sub>GS(off)</sub> = 12 V	4391		20	ns
		$V_{GS(off)} = 6.0 \text{ V}$	4392		35 50	ns
		$V_{GS(off)} = 3.0 \text{ V}$	4393			ns

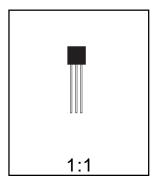
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  1.0%

### **TO-92 Package Dimensions**



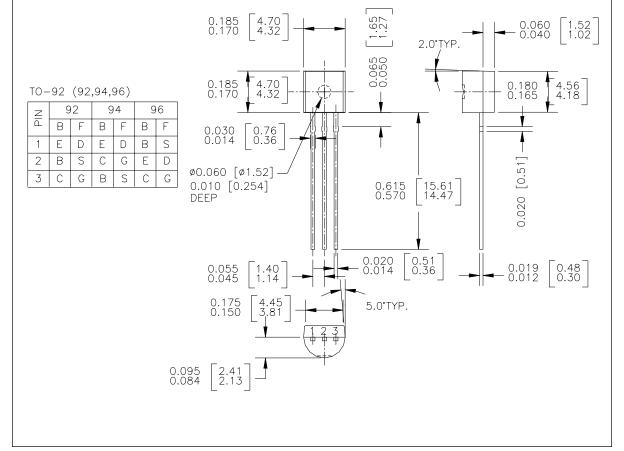
## TO-92 (FS PKG Code 92, 94, 96)





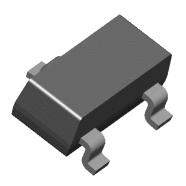
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

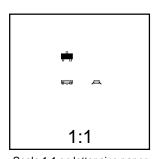
Part Weight per unit (gram): 0.1977





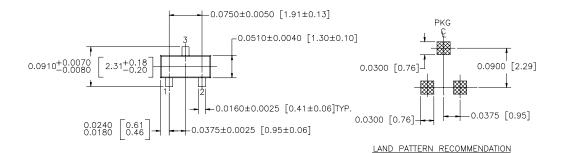
## SOT-23 (FS PKG Code 49)

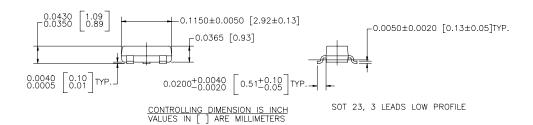




Scale 1:1 on letter size paper Dimensions shown below are in:

inches [millimeters]
Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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